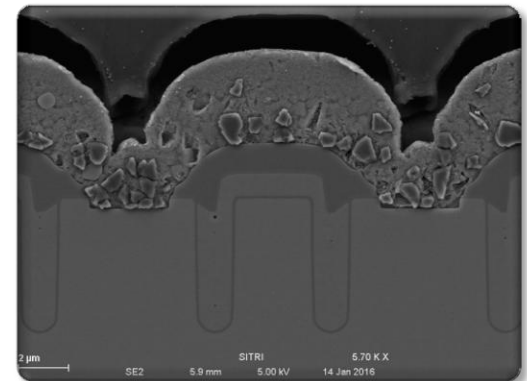
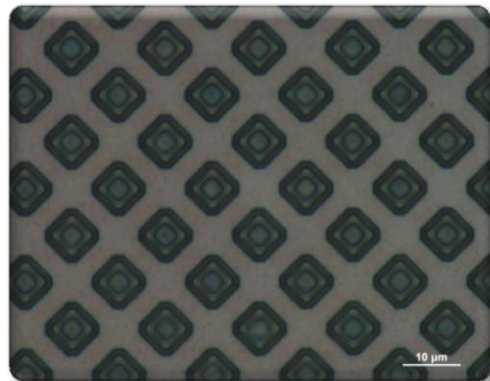


IHW20N120R5

Reverse Conducting IGBT with Monolithic Body Diode

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Product Analysis Report

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